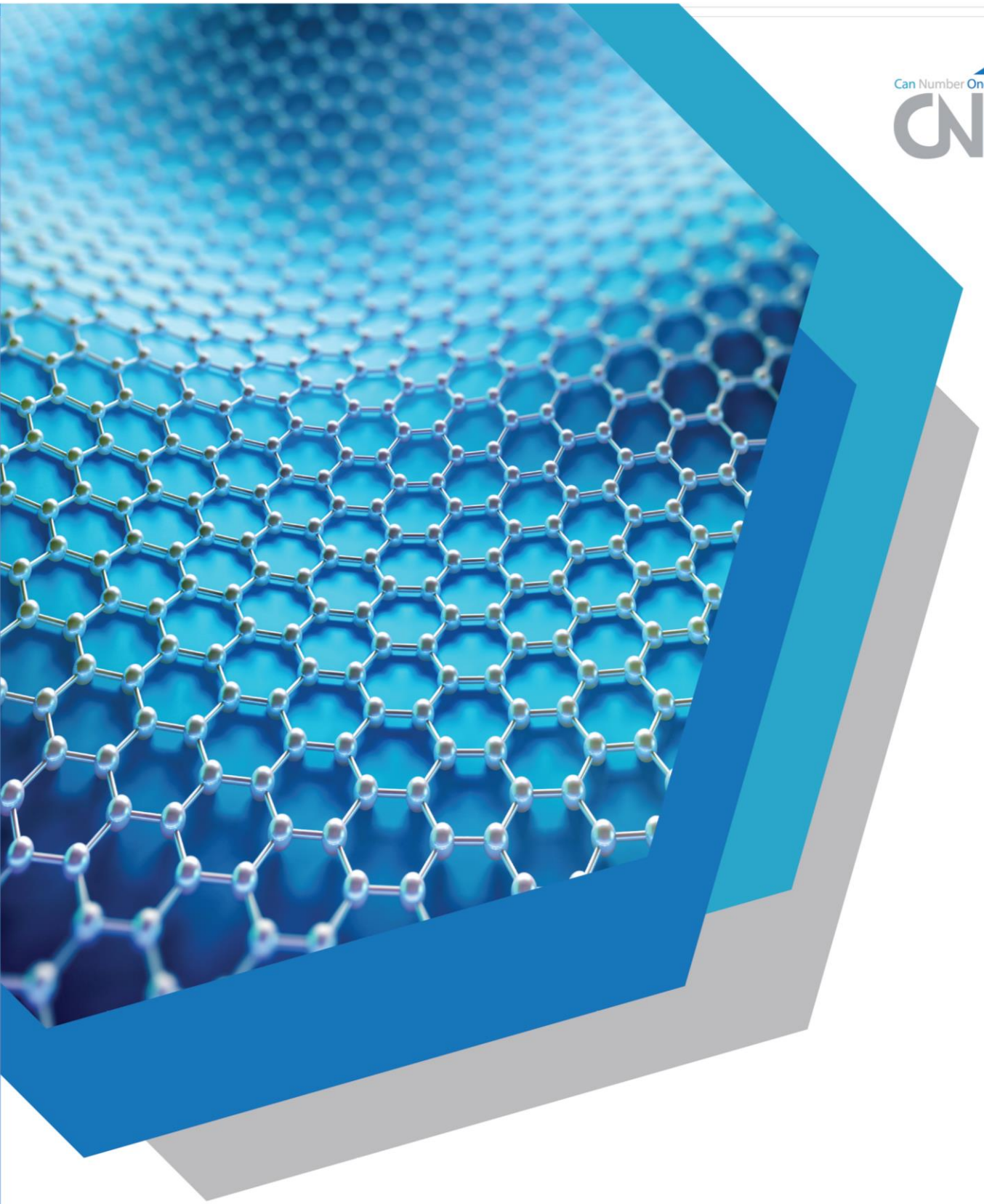


Creative Innovator for

Atomic Layer Deposition Technology

www.cn-1.co.kr

GREETING

CN1 has become the leading supplier of Atomic Layer Deposition (ALD) equipment through aggressive investments in R&D.

Our equipment designs and process technologies have been thoroughly proven and perfected over a decade of intensive development.

As a result, high-tech organizations working in the semiconductor, display, bio-tech and advanced energy industries now prefer CN1 ALD systems to meet their most demanding nanotechnology applications and production needs.

The proof is that CN1's ALD equipment is now in use at hundreds of leading Universities, Research Institutes and Companies in the United States, Japan, Singapore, Taiwan, Russia, China and Korea.

Our successes to date and our continual drive to grow as a global company demonstrate that CN1 truly "Can be the Number One".

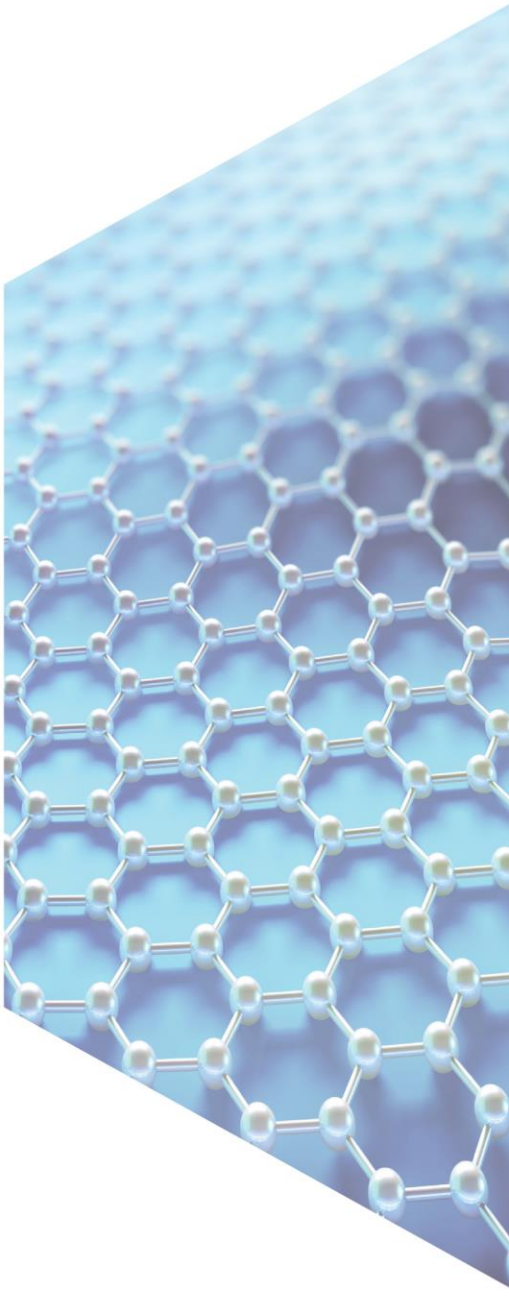
CEO
JH Jeong

Traveling Wave

ATOMIC CLASSIC

Available from 4″ to 8″ wafer

Thermal ALD Process



System Specification

Substrate Size : 4 ~ 8″ Standard (Wafer)
Thermal ALD Process
Laminar Gas Flow (Side Gas Flow)
Gas Delivery System : Bubbler, LDS etc.
Low Particle Generation
Small Volume for Process
Available Laminated & Mixed Process
Easy User Interface & Maintenance
Max Temperature : 450℃ (@ Wafer)
No. of Precursor Canisters : Up to 4 Sets (Standard)

Can Number One
CN1
#98-17, Dongtansandan 7-gil, Dongtan-myeon,
Hwaseong-si, Gyeonggi-do, 18487, KOREA
Tel 82 70 4651 5331
Fax 82 31 373 6002
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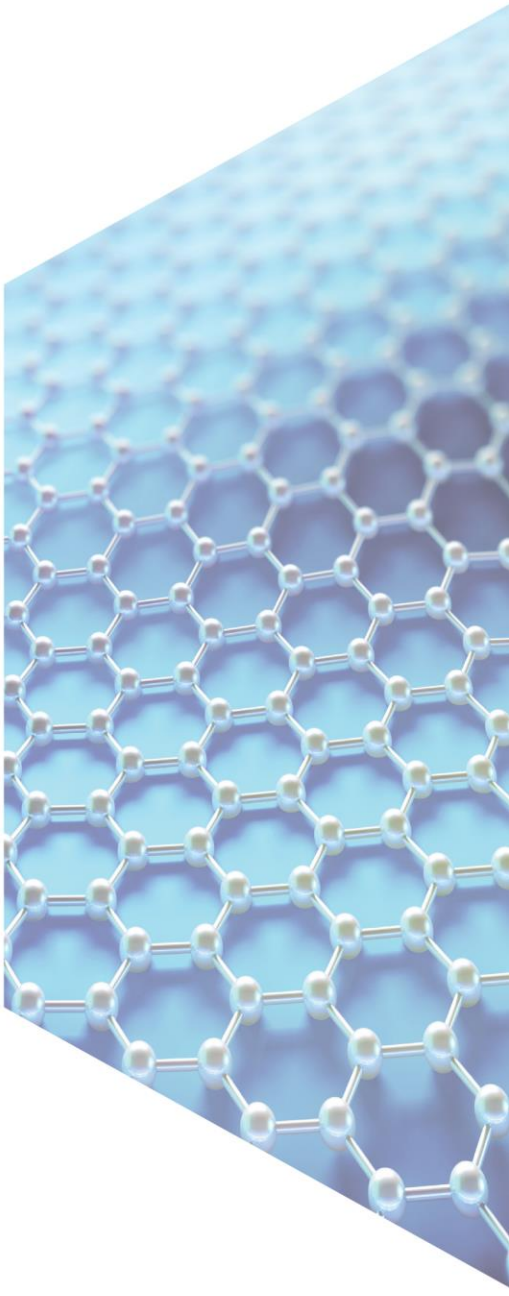
Showerhead

ATOMIC PREMIUM

Available from 4"to 12" wafer

Thermal & Plasma Enhanced ALD Process



System Specification

Substrate Size : 4 ~ 12" Standard (Wafer)
Thermal ALD Process (Plasma Process Available)
Chamber Material : Al6061 with Anodized
Gap Adjustable between Showerhead and Substrate
Gas Delivery System : Bubbler, LDS etc.
Max Temperature : 500℃ (@ Wafer)
No. of Precursor Canisters : Up to 4 Sets (Standard)
Pressure Control : Automatic Control by Throttle Valve
Process Gauge : CDG Gauge (10 Torr)
Process Pump : Dry Pump (Rotary Pump Available)
Pumping Line Hot Trap to Reduce Particle

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Batch Furnace

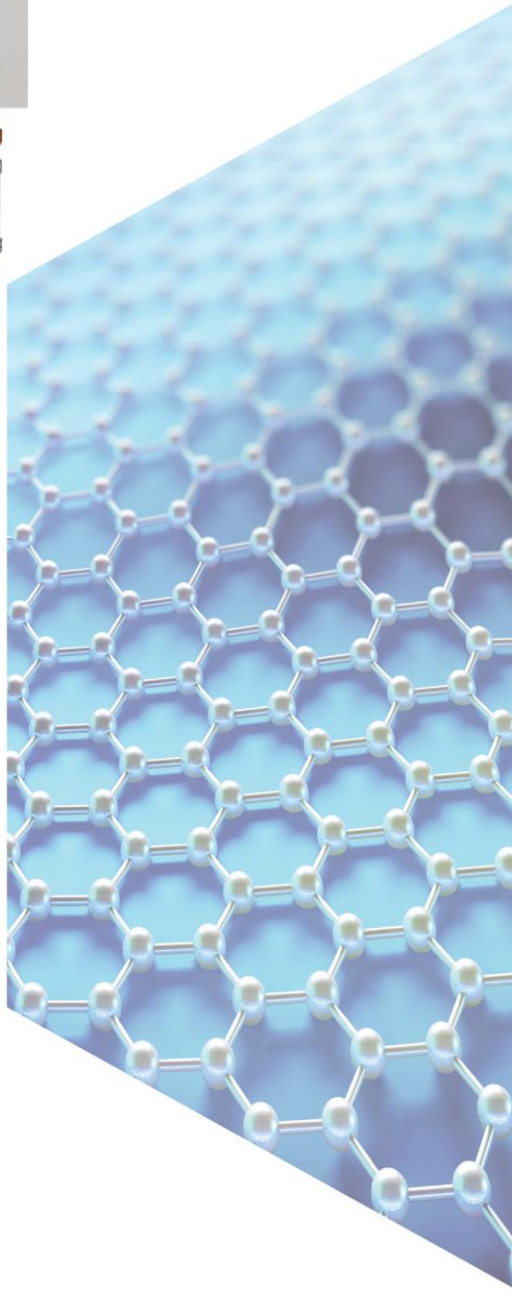
ATOMIC MEGA

Available from 4″ to 12″ multi wafers

Thermal ALD Process

System Specification

Vertical Furnace Type Batch ALD
Substrate Size : 4″ to 12″ Standard wafer
Product Wafer : 25EA / 50EA(up to 100EA)
Boat Slot Pitch : 10 ~ 15 ㎜
Boat Elevation System for Wafer Loading
Up/Down & Wafer Rotation
Manual / Automatic Wafer Transfer
Furnace Heater : Zone Temp. Control
Process Temp. : 400℃ ~ 800℃
Ramping-Up : > 10℃/min
Ramping-Down : 2 ~ 3.3℃/min



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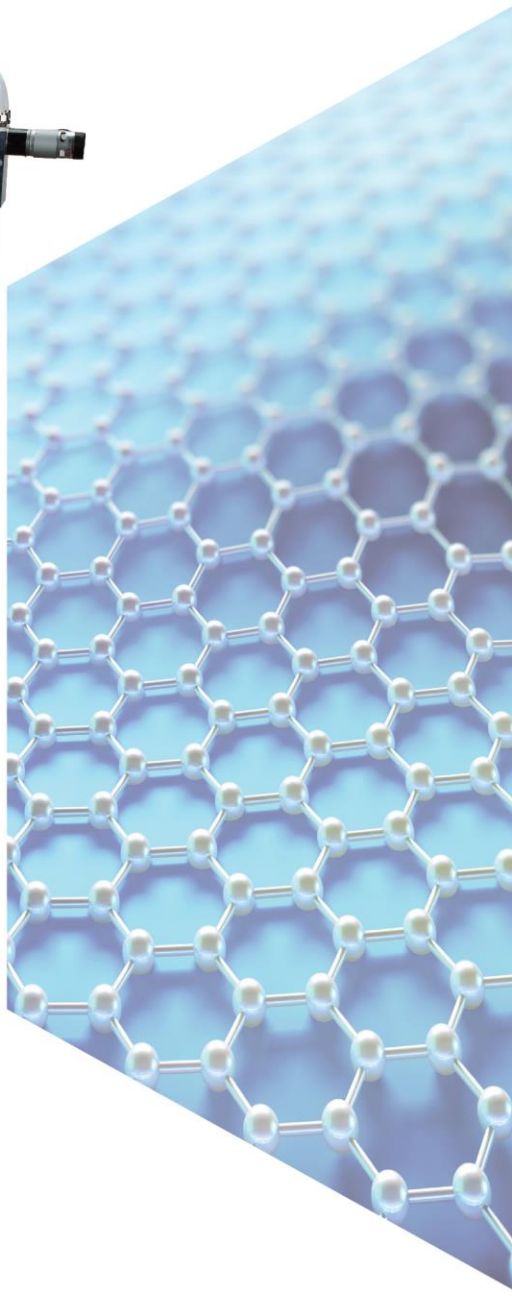
Rotatable Reactor

ATOMIC SHELL

Thermal ALD Process

For shell coating on core structure



System Specification

Reactor Volume : 100 cc ~ 500 cc
Filter Size : Variable (0.5 ㎛ ~)
Reactor Heating : Max 300 ℃ (Reactor Body : more than 230 ℃)
Reactor Rotation : DC Motor Driver
Rotation Speed : 10 ~ 60 rpm

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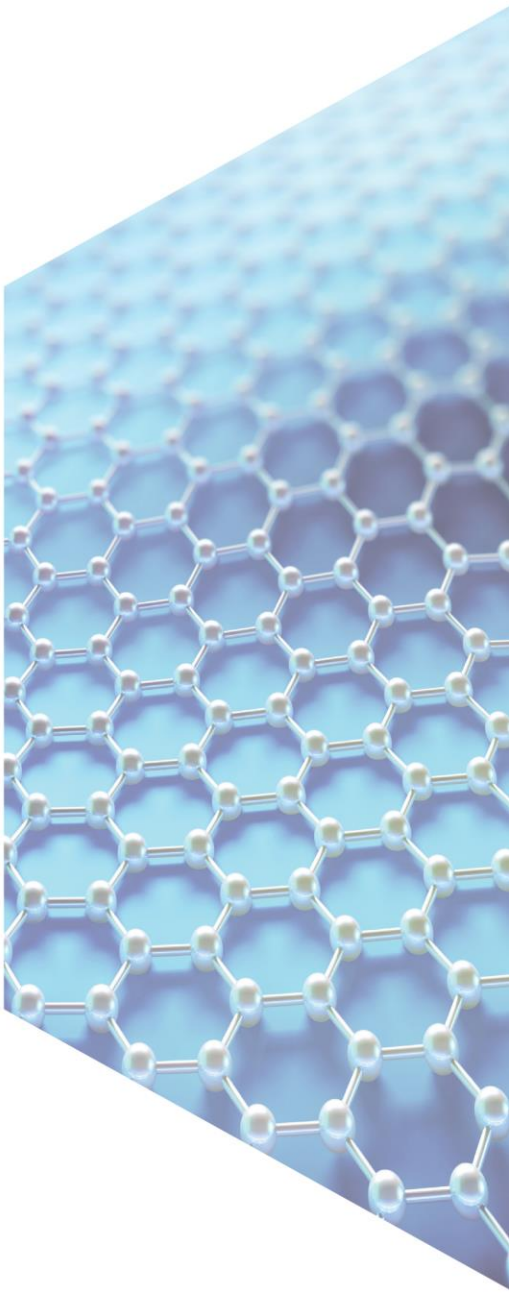
Undersize Reactor

ATOMIC BASIC

Simple & compact system

Thermal ALD Process



System Specification

Substrate Size : ≤6" Standard (Wafer)
Compact Reactor Thermal ALD
Very Small Volume for Process
Easy User Interface & Maintenance
Max Temperature : 300℃ (@ Wafer)

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